

Features

- Fast response time
- High sensitivity
- Small junction capacitance
- Pb Free
- This product itself will remain within RoHS compliant version
- Compliance with EU REACH
- Compliance Halogen Free(Br < 900ppm, Cl < 900ppm, Br+Cl < 1500ppm).



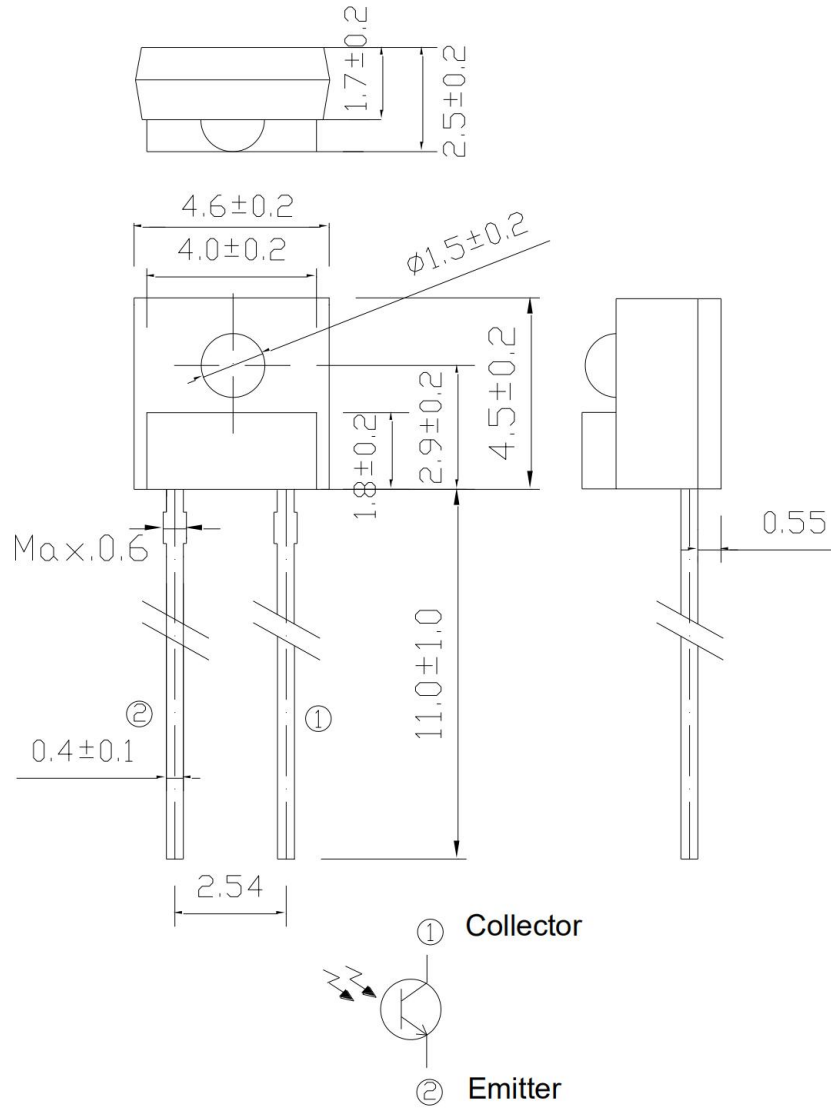
Application

- Optoelectronic switch
- VCR, Video Camera
- Floppy disk drive
- Infrared applied system

Description

ST-350B is a phototransistor in miniature package which is molded in a plastic with spherical top view lens. The device is spectrally matched to infrared emitting diode.

PACKAGE DIMENSIONS



NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25\text{mm}$ (.010") unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.

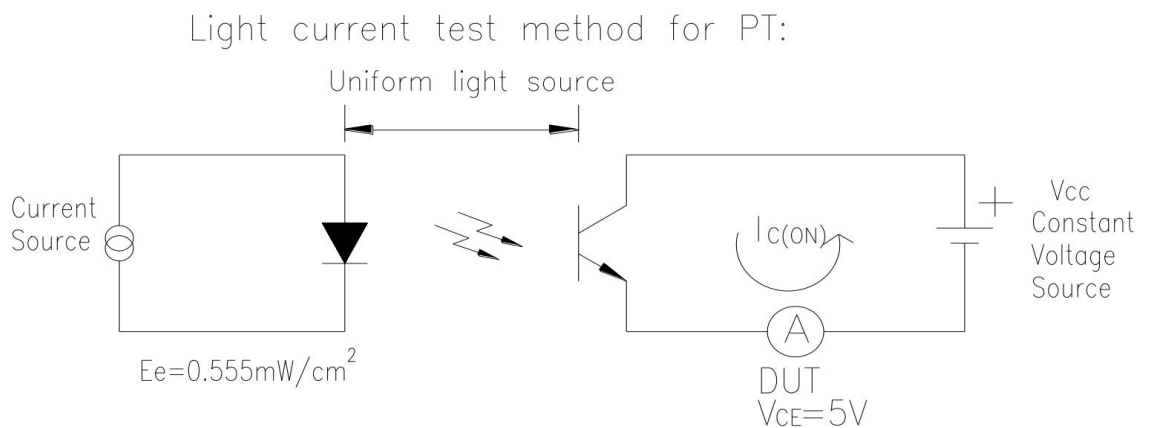
ABSOLUTE MAXIMUM RATINGS AT TA =25°C

| Parameter | Symbol | Rating | Units |
|---|-----------|-----------|-------|
| Collector-Emitter Voltage | V_{CEO} | 30 | V |
| Emitter-Collector Voltage | V_{ECO} | 5 | V |
| Collector Current | I_C | 20 | mA |
| Operating Temperature | T_{opr} | -25 ~ +85 | °C |
| Storage Temperature | T_{stg} | -40 ~ +85 | °C |
| Soldering Temperature *1 | T_{sol} | 260 | °C |
| Power Dissipation at (or below) 25 °C Free Air Temperature | P_d | 75 | mW |

Notes: *1 Soldering time \leq 5 seconds

ELECTRICAL OPTICAL CHARACTERISTICS AT TA=25°C

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Units |
|--------------------------------------|-----------------|-----------------------------------|------|------|------|-------|
| Rang of Spectral Bandwidth | $\lambda_{0.5}$ | ---- | 740 | -- | 1100 | nm |
| Wavelength of Peak Sensitivity | λ_p | ---- | -- | 940 | -- | nm |
| Collector-Emitter Breakdown Voltage | BV_{CEO} | $I_C=100\mu A$ $E_e=0mW/cm^2$ | 30 | -- | -- | V |
| Emitter-Collector Breakdown Voltage | BV_{ECO} | $I_E=100\mu A$ $E_e=0mW/cm^2$ | 5 | -- | -- | V |
| Collector Dark Current | I_{CEO} | $V_{CE}=20V$ $E_e=0mW/cm^2$ | -- | -- | 100 | nA |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=2mA$ $E_e=1mW/cm^2$ | -- | -- | 0.4 | V |
| On State Collector Current | $I_{C(on)}$ | $V_{CE}=5V$ $E_e=0.555mW/cm^2$ | 0.53 | -- | 3.41 | mA |

Test Method For $I_{C(ON)}$:Condition: $V_{CE}=5V$ $E_e=0.555mW/cm^2$ 

Typical Electro-Optical Characteristics Curves

Fig.1 Spectral Sensitivity

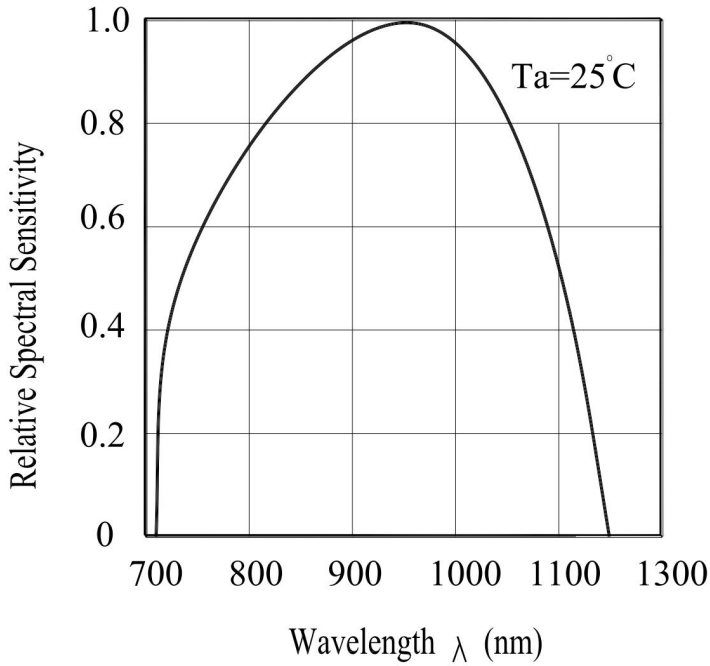


Fig.2 Collector Current Irradiance

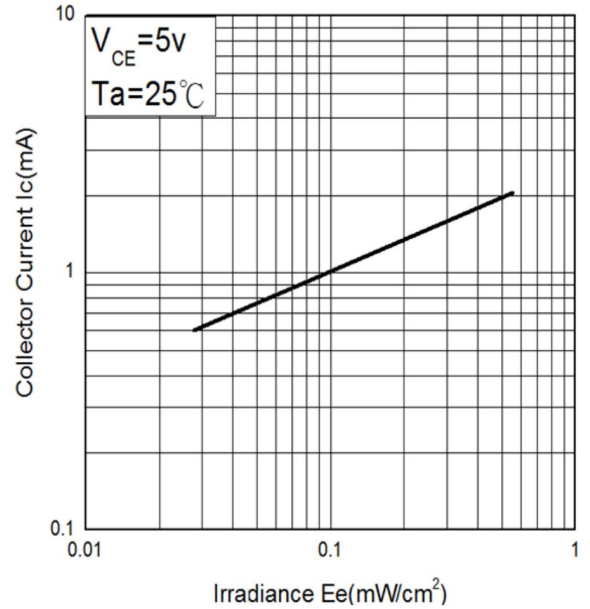
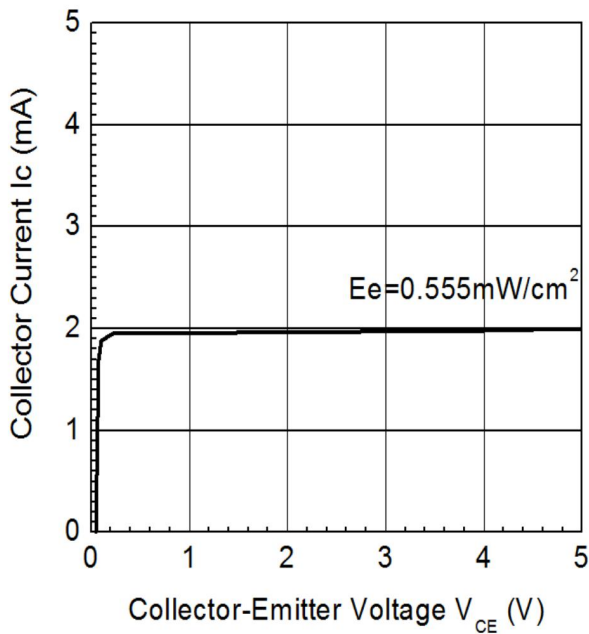


Fig.3 Collector Current vs. Collector-Emitter Voltage



Packing Quantity Specification

1. 1000Pcs/1Bag, 20 Bag/1Box
2. 4Boxes/1Carton

Label Form Specification

| | |
|--|--|
| 製品名 PRODUCT | |
| コードNo. CODE No. | |
| 数量 Q'TY | |
| ロットNo. LOT No. | |
| 備考 REMARKS | |
|  | |

- PRODUCT: Part Number
- CODE NO.: Product Serial Number
- QTY: Packing Quantity
- LOT No: Lot Number
- REMARKS:Remarks

Notes**Lead Forming**

1. During lead frame bending, the lead frame should be bent at a distance more than 3mm from bottom of the epoxy.

Note: Must fix lead frame and do not touch epoxy before bending to avoid Phototransistors broken.

2. Lead forming should be done before soldering.

3. Avoid stressing the Phototransistor package during leads forming. The stress to the base may damage the Phototransistor's characteristics or it may break the Phototransistors.

4. Cut the Phototransistor lead frame at room temperature. Cutting the lead frame at high temperatures may cause failure of the Phototransistors.

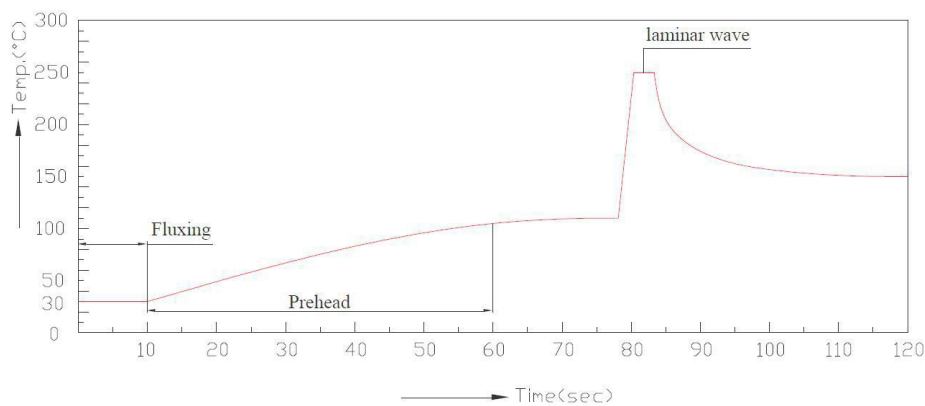
5. When mounting the Phototransistors onto a PCB, the PCB holes must be aligned exactly with the lead position of the Phototransistor. If the Phototransistors are mounted with stress at the leads, it causes deterioration of the epoxy resin and this will degrade the Phototransistors.

Soldering

- Careful attention should be paid during soldering. When soldering, leave more than 3mm from solder joint to epoxy bulb, and soldering beyond the base of the tie bar is recommended.
- Recommended soldering conditions:

| Hand Soldering | | DIP Soldering | |
|----------------------|---|-------------------|--|
| Temp. at tip of iron | 300°C Max. (30W Max.) | Preheat temp. | 100°C Max. (60 sec Max.) |
| Soldering time | 3 sec Max. | Bath temp. & time | 260 Max., 5 sec Max |
| Distance | 3mm Min.(From solder joint to epoxy bulb) | Distance | 3mm Min. (From solder joint to epoxy bulb) |

3. Recommended soldering profile



- Avoiding applying any stress to the lead frame while the Phototransistors are at high temperature particularly when soldering.
- Dip and hand soldering should not be done more than one time
- After soldering the Phototransistors, the epoxy bulb should be protected from mechanical shock or vibration until the Phototransistors return to room temperature.
- A rapid-rate process is not recommended for cooling the Phototransistors down from the peak temperature.
- Although the recommended soldering conditions are specified in the above table, dip or hand soldering at the lowest possible temperature is desirable for the Phototransistors.
- Wave soldering parameter must be set and maintain according to recommended temperature and dwell time in the solder wave.

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